BLM10D3438-70ABG

LDMOS 3-stage integrated Doherty MMIC

AMPLEON

Rev. 1 — 18 September 2020

Product data sheet

1. Product profile

1.1 General description

The BLM10D3438-70ABG is a 3-stage fully integrated Doherty MMIC solution using Ampleon's state of the art GEN10 LDMOS technology. The carrier and peaking device, input splitter and output combiner are integrated in a single package. This multiband device is perfectly suited as general purpose driver or mMIMO final in the frequency range from 3400 MHz to 3800 MHz. Available in gull wing.

Table 1. Performance

Typical RF performance at T_{case} = 25 °C; I_{Dq} = 110 mA (carrier); V_{GSq(peaking)} = V_{GSq(carrier)} - 0.5 V.

Test signal	f	V _{DS}	P _{L(M)}	Gp	ηם	ACPR _{20M}
	(MHz)	(V)	(dBm)	(dB)	(%)	(dBc)
1-carrier LTE 20 MHz	3600	28	40	31.8	37.8	-24

1.2 Features and benefits

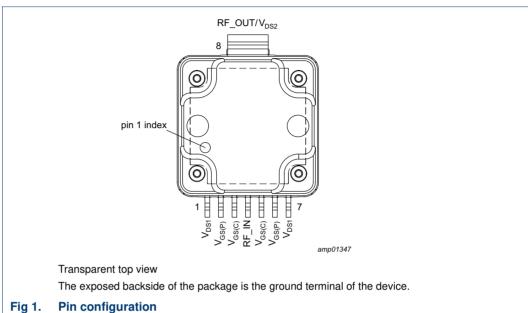
- Integrated input splitter
- Integrated output combiner
- High efficiency
- Designed for broadband operation (frequency 3400 MHz to 3800 MHz)
- Independent control of carrier and peaking bias
- Integrated ESD protection
- Source impedance 50 Ω ; high power gain
- For RoHS compliance see the product details on the Ampleon website

1.3 Applications

■ RF power MMIC for multi-carrier and multi-standard GSM, W-CDMA and LTE base stations in the 3400 MHz to 3800 MHz frequency range

2. Pinning information

2.1 Pinning



2.2 Pin description

Table 2. Pin description

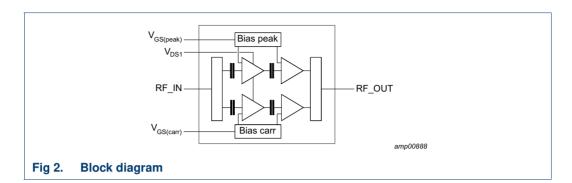
Symbol	Pin	Description
V _{DS1}	1	drain-source voltage of driver stages
V _{GS(P)}	2	gate-source voltage of peaking P
V _{GS(C)}	3	gate-source voltage of carrier C
RF_IN	4	RF input
V _{GS(C)}	5	gate-source voltage of carrier C
V _{GS(P)}	6	gate-source voltage of peaking P
V _{DS1}	7	drain-source voltage of driver stages
RF_OUT/V _{DS2}	8	RF output / drain-source voltage of final stages
GND	flange	RF ground

3. Ordering information

Table 3. Ordering information

Type number	Packag	je			
	Name	Description	Version		
BLM10D3438-70ABG		plastic, heatsink small outline package; 8 leads	OMP-400-8G-1		

4. Block diagram



5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	٧
V_{GS}	gate-source voltage		-6	+9	٧
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	200	°C
T _{case}	case temperature		-	150	°C

^[1] Continuous use at maximum temperature will affect the reliability. For details refer to the online MTF calculator.

6. Thermal characteristics

Table 5. Thermal characteristics

Measured for total device.

Symbol	Parameter	Conditions	Value	Unit
R _{th(j-c)}	thermal resistance from junction to	$T_{case} = 90 ^{\circ}C; P_{L} = 6.3 W$ [1]	1.88	K/W
	case	$T_{case} = 90 ^{\circ}C; P_{L} = 10 W$ [1]	1.51	K/W

^[1] When operated with a 1-carrier W-CDMA with PAR = 9.9 dB.

7. Characteristics

Table 6. DC characteristics

 $T_{case} = 25 \, ^{\circ}C$.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Carrier						'
V_{GSq}	gate-source quiescent voltage	$V_{DS} = 28 \text{ V}; I_D = 110 \text{ mA}$	1.6	2.2	2.7	V
I _{GSS}	gate leakage current	V _{GS} = 1 V; V _{DS} = 0 V	-	-	140	nA
Peaking						'
I _{GSS}	gate leakage current	$V_{GS} = 1 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	140	nA
Final sta	ges					
I _{DSS}	drain leakage current	$V_{GS} = 0 \text{ V}; V_{DS} = 28 \text{ V}$	-	-	1.4	μΑ
Driver st	Driver stages					
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 28 V	-	-	1.4	μΑ

Table 7. RF Characteristics

Typical RF performance at $T_{case} = 25$ °C; $V_{DS} = 28$ V; $I_{Dq} = 110$ mA (carrier); $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.5$ V; $P_{L(AV)} = 10$ W; unless otherwise specified measured in an Ampleon production circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Test sign	Test signal: pulsed CW [1]						
Gp	power gain	f = 3600 MHz	29.5	31.5	33.5	dB	
η_{D}	drain efficiency	P _L = 10 W (40 dBm)	33	42	-	%	
		$P_L = P_{L(3dB)}$	34	41	-	%	
RLin	input return loss		-	-15	-10	dB	
P _{L(3dB)}	output power at 3 dB gain compression		47.4	48.2	-	dBm	

^[1] Pulsed CW power sweep measurement (δ = 10 %, t_p = 100 μ s)

8. Application information

Table 8. Typical performance

 T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq} = 110 mA (driver and final stages); test signal: 1-carrier LTE 20 MHz, PAR 7.6 dB at 0.01 % probability CCDF; measured in an Ampleon 3400 MHz to 3800 MHz frequency band asymmetrical integrated Doherty application circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
P _{L(3dB)}	output power at 3 dB gain compression	f = 3600 MHz	1 -	48.6	-	dBm
$\phi_{s21}/\phi_{s21(norm)}$	normalized phase response	at 3 dB compression point; f = 3600 MHz	<u>l</u> -	-55.4	-	0
η _D	drain efficiency	8.6 dB OBO ($P_{L(AV)} = 40 \text{ dBm}$); f = 3600 MHz	-	37.3	-	%
G _p	power gain	P _{L(AV)} = 40 dBm; f = 3600 MHz	-	31.8	-	dB
B _{video}	video bandwidth	$P_{L(AV)} = 40$ dBm, set to obtain IMD3 = -40 dBc; 2-tone CW; f = 3600 MHz	-	>600	-	MHz
G _{flat}	gain flatness	$P_{L(AV)} = 40 \text{ dBm}$; f = 3400 MHz to 3800 MHz	-	0.5	-	dB

BLM10D3438-70ABG

LDMOS 3-stage integrated Doherty MMIC

Table 8. Typical performance ...continued

 $T_{case} = 25$ °C; $V_{DS} = 28$ V; $I_{Dq} = 110$ mA (driver and final stages); test signal: 1-carrier LTE 20 MHz, PAR 7.6 dB at 0.01 % probability CCDF; measured in an Ampleon 3400 MHz to 3800 MHz frequency band asymmetrical integrated Doherty application circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
ACPR _{20M}	adjacent channel power ratio (20 MHz)	P _{L(AV)} = 40 dBm; f = 3600 MHz	-	-24.4	-	dBc
ΔG/ΔT	gain variation with temperature	f = 3600 MHz	-	0.06	-	dB/°C
К	Rollett stability factor	$T_{case} = -40 ^{\circ}\text{C}; f = 0.2 \text{GHz to}$ 6 GHz	-	>1.5	-	

- [1] Pulsed CW power sweep measurement (δ = 10 %, t_p = 100 μ s).
- [2] 25 ms CW power sweep measurement.
- [3] S-parameters measured with broadband demo board.

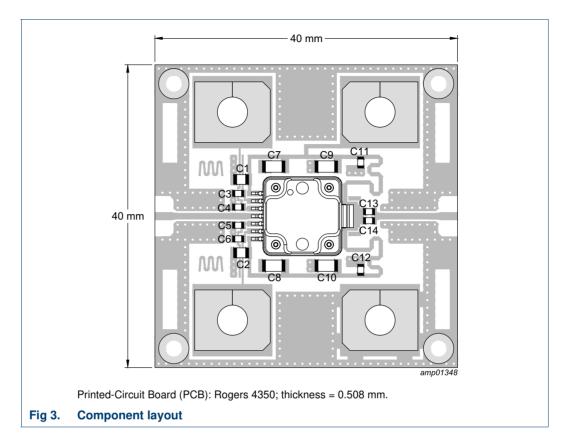


Table 9. Demo test circuit list of components

See Figure 3 for component layout.

Component	Description	Value	Remarks
C1, C2	multilayer ceramic chip capacitor	4.7 μF, 35 V	TDK
C3, C4, C5, C6	multilayer ceramic chip capacitor	1 μF, 6.3 V	Murata
C7, C8, C9, C10	multilayer ceramic chip capacitor	10 μF, 50 V	Murata
C11, C12	multilayer ceramic chip capacitor	3 pF	Murata
C13, C14	multilayer ceramic chip capacitor	4.7 pF	Murata

8.1 Ruggedness in a Doherty operation

The BLM10D3438-70ABG is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: $V_{DS} = 32 \text{ V}$; $I_{Dq} = 110 \text{ mA (carrier)}$; $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.5 \text{ V}$; P_i corresponding to $P_{L(3dB)} - 5 \text{ dB}$ under $Z_S = 50 \Omega$ load; f = 3800 MHz (1-carrier W-CDMA signal with PAR = 9.9 dB); $T_{case} = 25 \,^{\circ}\text{C}$ unless otherwise specified.

8.2 Impedance information

Table 10. Typical impedance for optimum Doherty operation

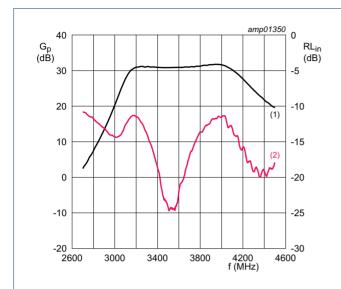
Measured load-pull data per section; test signal: pulsed CW; T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq} = 110 mA (carrier); $V_{GSq(peaking)}$ = $V_{GSq(carrier)}$ – 0.5 V; t_p = 100 μ s; δ = 10 %. Typical values unless otherwise specified.

	tuned for optimur	tuned for optimum Doherty operation					
f	Z _L	G _{p(max)}	P _{L(3dB)}	η _{add} [1]	η _{add} [2]		
(MHz)	(Ω)	(dB)	(dBm)	(%)	(%)		
3400	19.51 – j22.94	32.4	48.48	43.3	44.0		
3500	19.86 – j19.85	32.0	48.59	44.1	45.0		
3600	17.03 – j17.98	32.1	48.65	44.9	45.4		
3700	15.13 – j18.50	32.2	48.67	45.5	45.1		
3800	14.85 – j20.56	32.8	48.68	46.4	44.2		

^[1] At 3 dB gain compression point.

^[2] At $P_L = 40 \text{ dBm}$.

8.3 Graphs



 $T_{case} = 25 \, ^{\circ}C; \, V_{DS} = 28 \, V;$

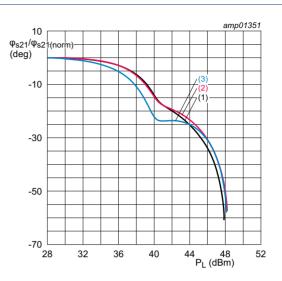
 $I_{Dq1} + I_{Dq2} = 110$ mA (carrier and peaking stages); $V_{GS} = 2.11$ V (carrier stage);

V_{GS} = 1.61 V (peaking stage).

Test signal: CW.

- (1) magnitude of G_p
- (2) magnitude of RLin

Fig 5. Wideband power gain and input return loss as function of frequency; typical values



 $T_{case} = 25 \, ^{\circ}C; \, V_{DS} = 28 \, V;$

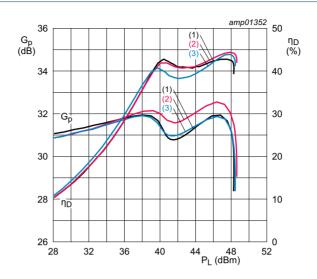
 $I_{Dq1} + I_{Dq2} = 110$ mA (carrier and peaking stages); $V_{GS} = 2.11$ V (carrier stage);

V_{GS} = 1.61 V (peaking stage).

Test signal: 25 ms CW power sweep.

- (1) f = 3400 MHz
- (2) f = 3600 MHz
- (3) f = 3800 MHz

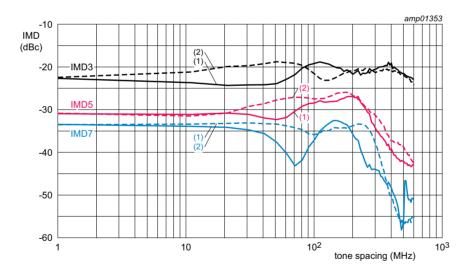
Fig 6. Normalized phase response as a function of output power; typical values



 T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} + I_{Dq2} = 110 mA (carrier and peaking stages); V_{GS} = 2.11 V (carrier stage); V_{GS} = 1.61 V (peaking stage). Test signal: pulsed CW power sweep (δ = 10 %; t_p = 100 μs).

- (1) f = 3400 MHz
- (2) f = 3600 MHz
- (3) f = 3800 MHz

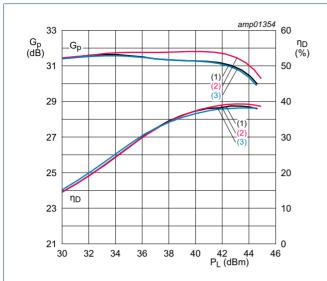
Fig 7. Power gain and drain efficiency as function of output power; typical values



 T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} + I_{Dq2} = 110 mA (carrier and peaking stages); V_{GS} = 2.11 V (carrier stage); V_{GS} = 1.61 V (peaking stage). Test signal: 2-tone CW; f_c = 3600 MHz.

- (1) IMD low
- (2) IMD high

Fig 8. Intermodulation distortion as a function of tone spacing; typical values



 $T_{case} = 25 \, ^{\circ}C; \, V_{DS} = 28 \, V;$

 $I_{Dq1} + I_{Dq2} = 110$ mA (carrier and peaking stages);

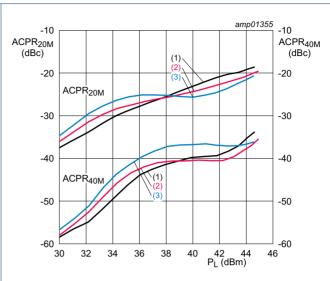
V_{GS} = 2.11 V (carrier stage);

V_{GS} = 1.61 V (peaking stage).

Test signal: 1-carrier LTE; PAR = 7.6 dB at 0.01 % probability CCDF.

- (1) f = 3400 MHz
- (2) f = 3600 MHz
- (3) f = 3800 MHz

Fia 9. Power gain and drain efficiency as function of output power; typical values



 $T_{case} = 25 \, ^{\circ}C; \, V_{DS} = 28 \, V;$

 $I_{Dq1} + I_{Dq2} = 110$ mA (carrier and peaking stages);

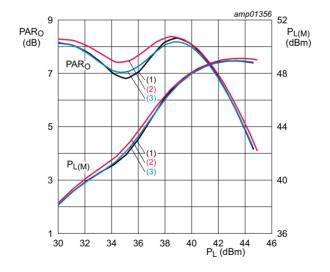
V_{GS} = 2.11 V (carrier stage);

V_{GS} = 1.61 V (peaking stage).

Test signal: 1-carrier LTE; PAR = 7.6 dB at 0.01 % probability CCDF.

- (1) f = 3400 MHz
- (2) f = 3600 MHz
- (3) f = 3800 MHz

Fig 10. Adjacent channel power ratio as a function of output power; typical values



 T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} + I_{Dq2} = 110 mA (carrier and peaking stages);

V_{GS} = 2.11 V (carrier stage); V_{GS} = 1.61 V (peaking stage).

Test signal: 1-carrier LTE; PAR = 7.6 dB at 0.01 % probability CCDF.

- (1) f = 3400 MHz
- (2) f = 3600 MHz
- (3) f = 3800 MHz

Fig 11. Output peak-to-average ratio and peak output power as function of output power; typical values

9. Package outline

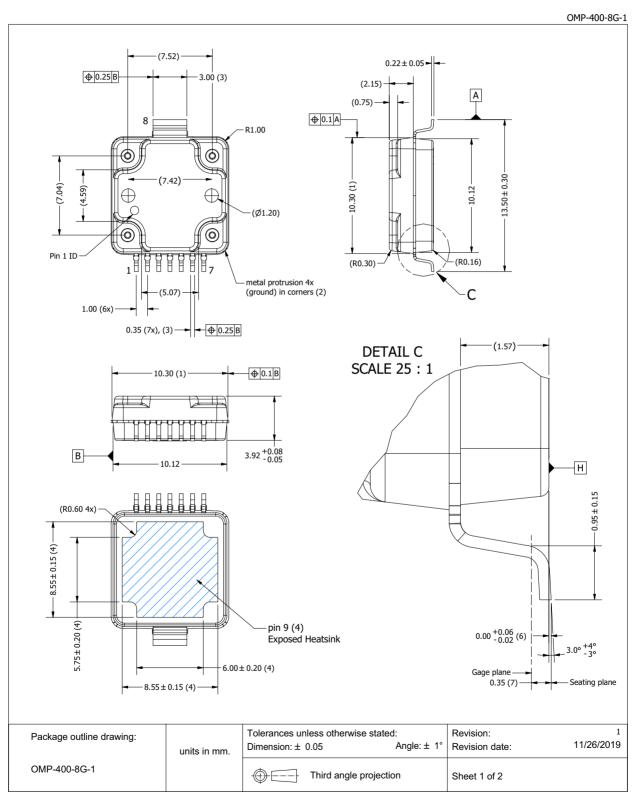


Fig 12. Package outline OMP-400-8G-1 (sheet 1 of 2)

OMP-400-8G-1

	Drawing Notes
Items	Description
	Dimensions are excluding mold protrusion. Areas located adjacent to the leads have a maximum mold protrusion of 0.25
(1)	mm (per side) and 0.62 mm max. in length. In between the 7 leads the protrusion is 0.25 mm max. At all other areas the
	mold protrusion is maximum 0.15 mm per side. See also detail B.
(2)	The metal protrusion (tie bars) in the corner will not stick out of the molding compound protrusions (detail A).
(3)	The lead dambar (metal) protrusions are not included. Add 0.14 mm max to the total lead dimension at the dambar location
(4)	The hatched area indicates the exposed heatsink. The dimensions represent the values between two opposite points along
(4)	the original heatsink perimeter.
(5)	The leads and exposed heatsink are plated with matte Tin (Sn).
(0)	Dimension is measured with respect to the bottom of the heatsink Datum H. Positive value means that the bottom of the
(6)	heatsink is higher than the bottom of the lead.
(7)	Gage plane (foot length) to be measured from the seating plane.

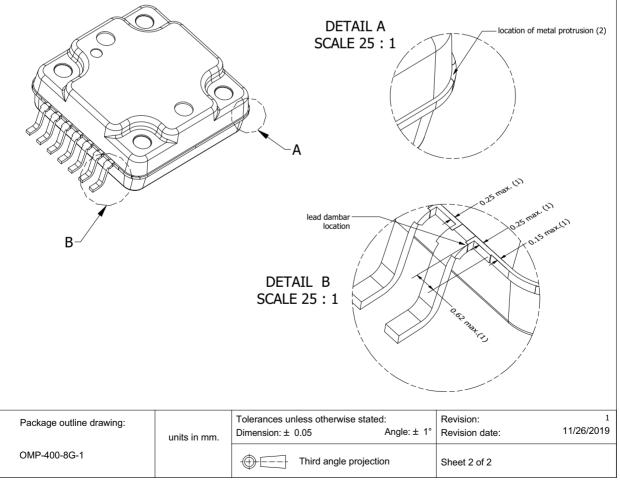


Fig 13. Package outline OMP-400-8G-1 (sheet 2 of 2)

10. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 11. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C1 🗓
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	1B 🔼

- [1] CDM classification C1 is granted to any part that passes after exposure to an ESD pulse of 250 V.
- [2] HBM classification 1B is granted to any part that passes after exposure to an ESD pulse of 500 V.

11. Abbreviations

Table 12. Abbreviations

Acronym	Description
CW	Continuous Wave
ESD	ElectroStatic Discharge
GEN10	Tenth Generation
GSM	Global System for Mobile Communications
LDMOS	Laterally Diffused Metal Oxide Semiconductor
LTE	Long Term Evolution
mMIMO	Massive Multiple Input-Multiple Output
MMIC	Monolithic Microwave Integrated Circuit
MTF	Median Time to Failure
ОВО	Output Back Off
PAR	Peak-to-Average Ratio
RoHS	Restriction of Hazardous Substances
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

12. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLM10D3438-70ABG v.1	20200918	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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